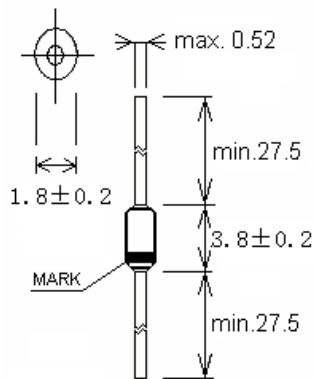


## 1N4148/1N4448/1N914B

## DO-35 Glass

 DO-35 玻封开关二极管  
DO-35 Glass Switching Diode


Unit: mm

**特征 Features**

- 开关速度小于 4.0nS; Fast Switching Device (TRR <4.0 nS)
- 最大功率耗散 500mW; Power Dissipation of 500mW
- 高稳定性和可靠性。High Stability and High Reliability
- 反向漏电流小。Low reverse leakage

**机械数据 Mechanical Data**

- 封装: DO-35 玻璃封装 Case: DO-35 Glass Case
- 极性: 色环端为负极 Polarity: Color band denotes cathode end
- 安装位置: 任意 Mounting Position: Any

**极限值和温度特性**(TA = 25°C 除非另有规定)

**Maximum Ratings & Thermal Characteristics** (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
反向电压 Reverse Voltage	V <sub>R</sub>	75	V
反向峰值电压 Peak Reverse Voltage	V <sub>RM</sub>	100	V
功率消耗 Power Dissipation	P <sub>d</sub>	500	mW
工作结温 Operating junction temperature	T <sub>j</sub>	175	°C
存储温度 Storage temperature range	T <sub>s</sub>	-65-+200	°C
反向工作电压 Working Inverse Voltage	W <sub>IV</sub>	75	V
平均整流电流 Average Rectified Current	I <sub>o</sub>	150	mA
正向(不重复)电流 Non-repetitive Peak Forward Current @ t<1s and T <sub>j</sub> =25°C	I <sub>FM</sub>	450	mA

Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

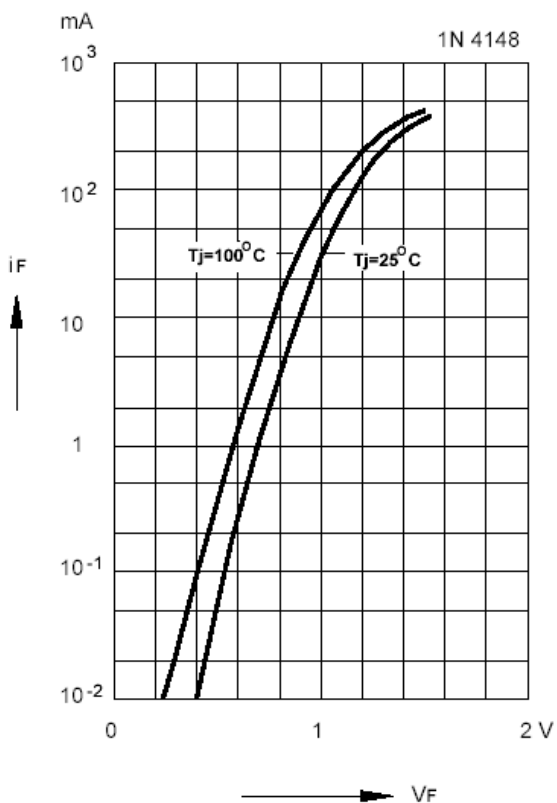
**电特性** (TA = 25°C 除非另有规定)

**Electrical Characteristics** (Ratings at 25°C ambient temperature unless otherwise specified).

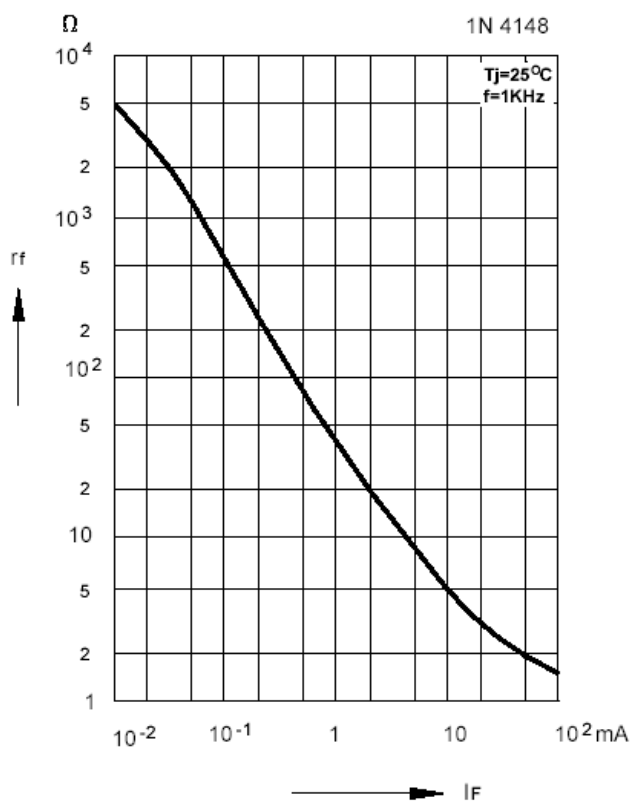
符号 Symbols	参数 Parameter	测试条件 Test Condition	界限 Limits		单位 Unit
			Min	Max	
BV	反向击穿电压 Breakdown Voltage	IR=100uA	100		V
		IR=5uA	75		
IR	反向漏电流 Reverse Leakage Current	VR=20V	---	25	nA
		VR=75	---	5	uA
VF	正向电压 Forward Voltage	1N4448/1N914B IF=5mA	0.62	0.72	V
		1N4148 IF=10mA	---	1	
		1N4448/1N914B IF=100mA	---	1	
TRR	反向恢复时间 Reverse Recovery Time	IF= 10mA, IR=1.0mA RL=100Ω IRR=1mA	---	4	nS
C	结电容 Capacitance	VR=0V, f=1MHZ	---	4	pF

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Forward characteristics

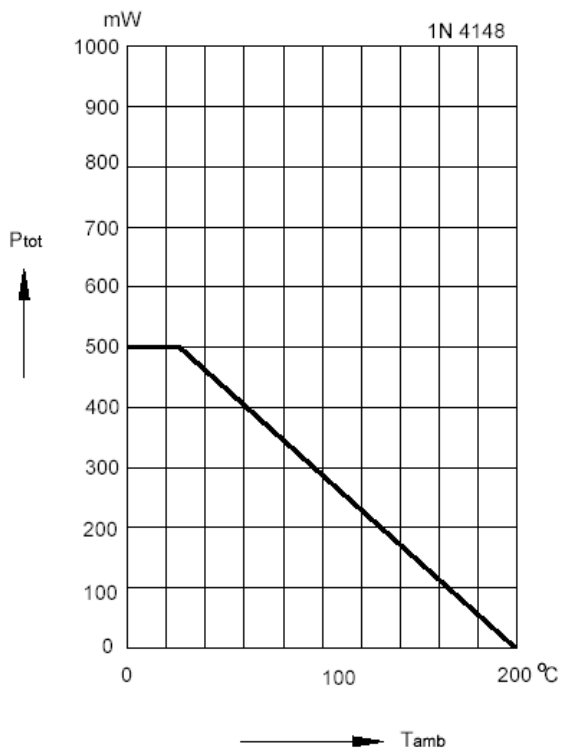


Dynamic forward resistance versus forward current

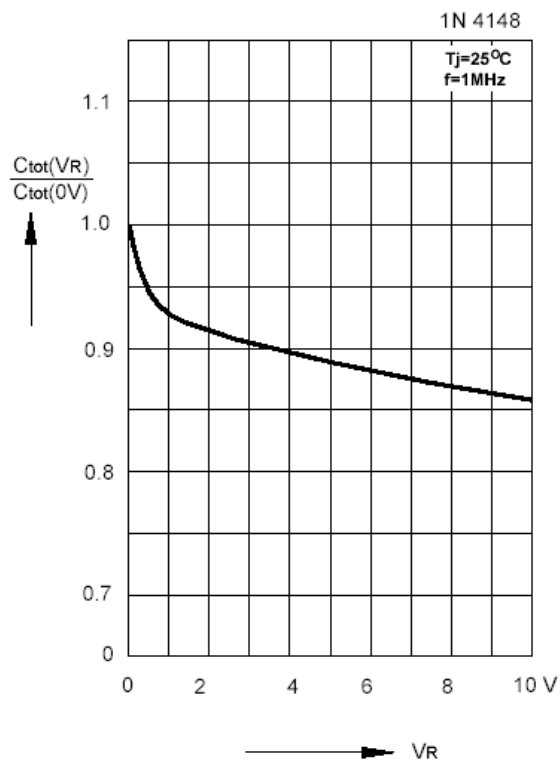


Admissible power dissipation versus ambient temperature

Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature

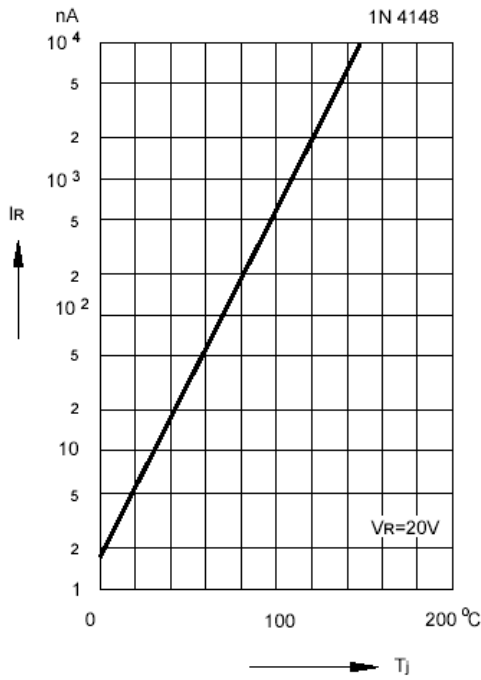


Relative capacitance versus reverse voltage



1N4148/1N4448/1N914B

Leakage current versus junction temperature



Admissible repetitive peak forward current versus pulse duration

Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature

